Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V	
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	18	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	51	W	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C		-	59	69	mΩ	
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C		-	-	86	mΩ	
		V _{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 13</u>		-	65	77	mΩ	
Avalanche rug	Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 18 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	33	mJ	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	G T A
mb	D	mounting base; connected to drain	1 3	mbb076 S
			DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK9277-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			
BUK9277-55A/CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9277-55A	BUK9277-55A
BUK9277-55A/CD	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	51	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	18	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	13	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3		-	73	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	diode				•	,
I _S	source current	T _{mb} = 25 °C		-	18	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	73	Α
Avalanche ruç	ggedness				•	,
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 18 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	33	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	Fig. 4	[1][2][3][<u>4]</u>	-	J

- [1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.
- [4] Refer to application note AN10273 for further information.

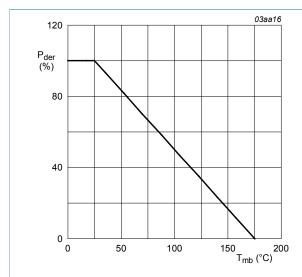


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

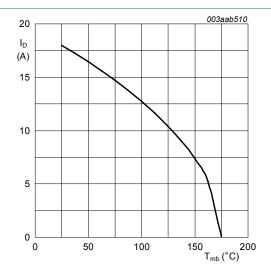


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{\rm GS} \geq 5\,V$$

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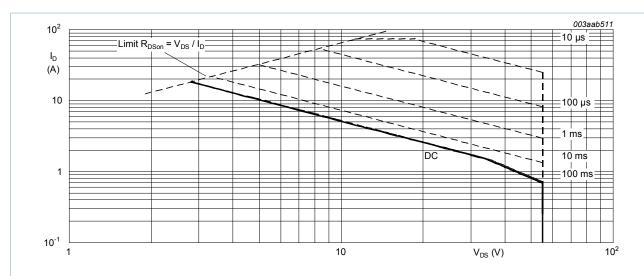


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25 \,^{\circ}C; I_{DM}$$
 is single pulse

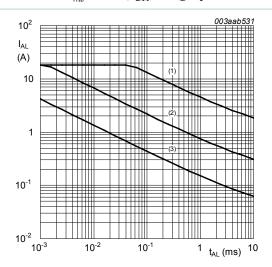


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

(1) Single-pulse; $T_j = 25 \, {}^{\circ}C$.

(2) Single-pulse; $T_j = 150 \, ^{\circ}C$.

(3) Repetitive.

9. Thermal characteristics

Table 6. Thermal characteristics

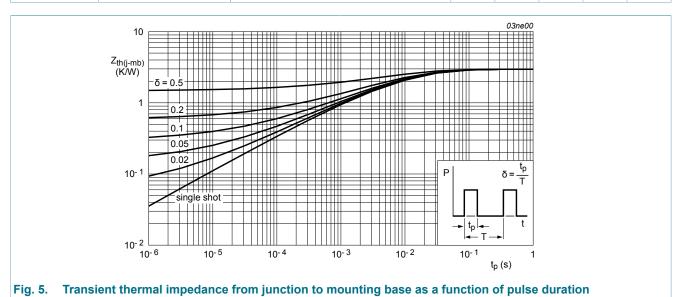
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	2.93	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	71.4	-	K/W



10. Characteristics

Table 7. Characteristics

cteristics drain-source				_	
drain-source					
	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	55	-	-	V
breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 12	-	-	2.3	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 12	1	1.5	2	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 12	0.5	-	-	V
drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μΑ
gate leakage current	V _{GS} = 15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
	V _{GS} = -15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
drain-source on-state	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C	-	59	69	mΩ
resistance	V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C	-	-	86	mΩ
	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 175 ^{\circ}\text{C};$ Fig. 13	-	-	154	mΩ
	gate-source threshold voltage drain leakage current gate leakage current drain-source on-state			$ \begin{array}{c} I_D = 0.25 \ \text{mA}, \ V_{GS} = 0 \ \text{V}, \ I_j = -55 \ \text{C} \\ \hline \\ \text{gate-source threshold} \\ \text{voltage} \\ \\ \hline \\ I_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 12 \\ \hline \\ I_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 12 \\ \hline \\ I_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 12 \\ \hline \\ \text{drain leakage current} \\ \hline \\ \text{VDS} = 55 \ \text{V}; \ V_{GS} = 0 \ \text{V}; \ T_j = 175 \ ^{\circ}\text{C} \\ \hline \\ V_{DS} = 55 \ \text{V}; \ V_{GS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ \text{V}_{GS} = 15 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ \text{V}_{GS} = -15 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ \text{V}_{GS} = 10 \ \text{V}; \ I_D = 10 \ \text{A}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ \text{V}_{GS} = 5 \ \text{V}; \ I_D = 10 \ \text{A}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ \text{V}_{GS} = 5 \ \text{V}; \ I_D = 10 \ \text{A}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \hline \\ \text{Fig. 13} \\ \hline \end{array}$	$ \begin{array}{c} \text{I}_D = 0.25 \text{ filA}, \ V_{GS} = 0 \text{ V}, \ I_j = -55 \text{ °C} \\ \text{gate-source threshold} \\ \text{voltage} \\ \\ \hline \\ I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \text{ °C}; \\ \hline \\ Fig. \ 12 \\ \hline \\ I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}; \ T_j = 25 \text{ °C}; \\ \hline \\ Fig. \ 12 \\ \hline \\ I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}; \ T_j = 175 \text{ °C}; \\ \hline \\ Fig. \ 12 \\ \hline \\ \text{drain leakage current} \\ \hline \\ V_{DS} = 55 \text{ V}; \ V_{GS} = 0 \text{ V}; \ T_j = 175 \text{ °C} \\ \hline \\ V_{DS} = 55 \text{ V}; \ V_{GS} = 0 \text{ V}; \ T_j = 25 \text{ °C} \\ \hline \\ V_{GS} = 15 \text{ V}; \ V_{DS} = 0 \text{ V}; \ T_j = 25 \text{ °C} \\ \hline \\ V_{GS} = -15 \text{ V}; \ V_{DS} = 0 \text{ V}; \ T_j = 25 \text{ °C} \\ \hline \\ V_{GS} = 10 \text{ V}; \ I_D = 10 \text{ A}; \ T_j = 25 \text{ °C} \\ \hline \\ V_{GS} = 5 \text{ V}; \ I_D = 10 \text{ A}; \ T_j = 25 \text{ °C} \\ \hline \\ V_{GS} = 5 \text{ V}; \ I_D = 10 \text{ A}; \ T_j = 175 \text{ °C}; \\ \hline \\ Fig. \ 13 \\ \hline \\ \hline \\ \end{array}$

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Symbol	Parameter	Conditions	Mii	п Тур	Max	Unit
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 13$	-	65	77	mΩ
Dynamic cl	haracteristics			1	'	,
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 5 \text{ V};$	-	11	-	nC
Q _{GS}	gate-source charge	Fig. 14	-	1.6	-	nC
Q_{GD}	gate-drain charge		-	5	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-	440	643	pF
C _{oss}	output capacitance		-	90	110	pF
C _{rss}	reverse transfer capacitance		-	60	93	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 10 \Omega; T_j = 25 \text{ °C}$	-	10	-	ns
t _r	rise time		-	47	-	ns
t _{d(off)}	turn-off delay time		-	28	-	ns
t _f	fall time		-	33	-	ns
L _D	internal drain inductance	meausured from drain lead from package to centre of die; T _j = 25 °C	-	2.5	-	nH
L _S	internal source inductance	measured from source lead from package to source bond pad; T _j = 25 °C	-	7.5	-	nH
Source-dra	in diode			1		
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	33	-	ns
Q _r	recovered charge		-	60	-	nC

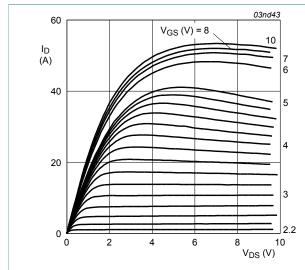


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25^{\circ}C; t_p = 300\mu s$$

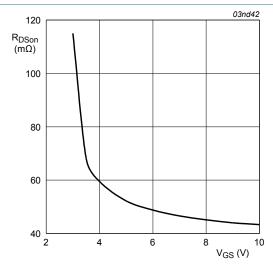


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

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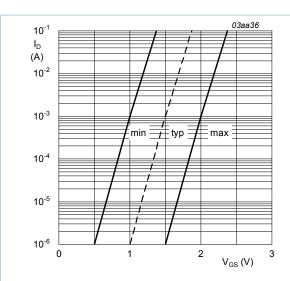


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$$T_j=25\,^{\circ}C; V_{DS}=V_{GS}$$

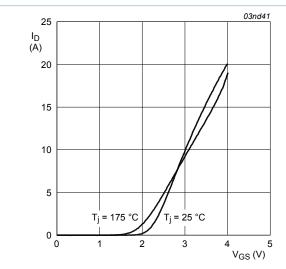


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 25V$$

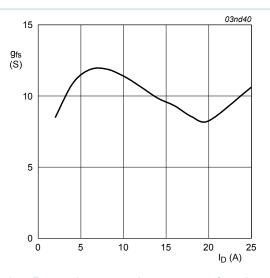


Fig. 9. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; V_{DS} = 25V$$

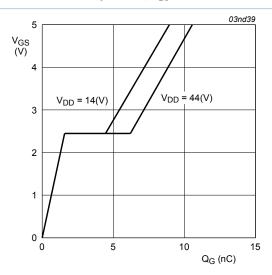


Fig. 11. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

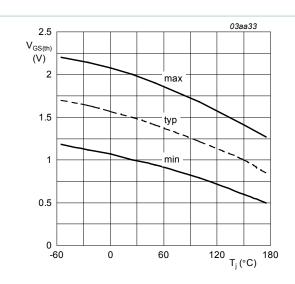


Fig. 12. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

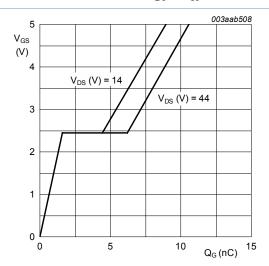


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 10A$$

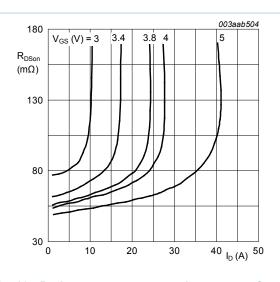


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

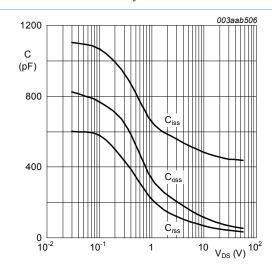


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

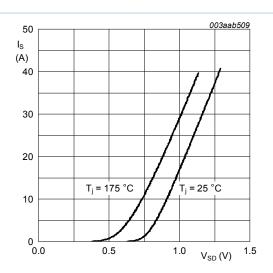
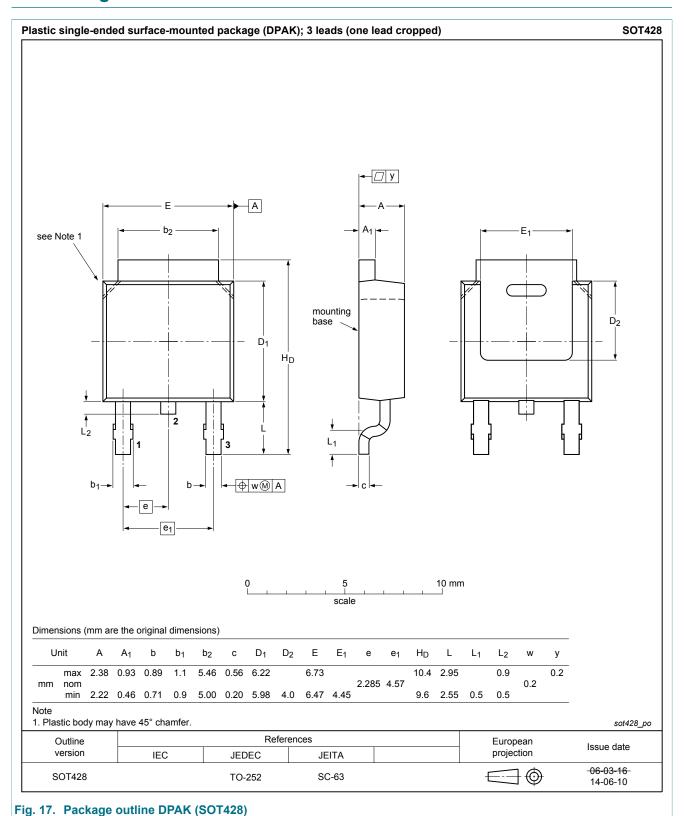


Fig. 16. Source current as a function of source-drain voltage; typical values

$$V_{\rm GS} = 0\,V$$

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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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